

Nonlinear theory of fractional microwave-induced magnetoresistance oscillations in a dc-driven two-dimensional electron system

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Microwave-induced nonlinear magnetoresistance in a dc-driven two-dimensional electron system is examined at low temperatures using a multi-photon-assisted magnetotransport scheme direct controlled by the current. It is shown that near the 2nd and 3rd subharmonics of the cyclotron resonance, $\omega/\omega_c = 1/2$ and $1/3$ (ω_c and ω are the cyclotron and microwave frequency), the frequency of the resistivity oscillations with the normalized current-density parameter $\epsilon_j \equiv \omega_j/\omega_c$ ($\omega_j = 2k_F v$, k_F is the Fermi wave vector and v is the dc drift velocity) is respectively double and triple that of the oscillations at the cyclotron resonance and its harmonics, $\omega/\omega_c = 1, 2, 3, \dots$. The current-induced alternative emergence of resonant two-photon and single-photon processes near $\omega/\omega_c = 1/2$, and the current-induced consecutive appearance of resonant 0-/3-, 2-, 1-, 0-/3-, 1-/2-, and 2-/1-photon processes near $\omega/\omega_c = 1/3$, are responsible for the frequency doubling and tripling. These predictions are in excellent agreement with recent experimental findings by Hatke *et al.*

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A number of extraordinary magnetotransport phenomena of irradiated two-dimensional (2D) electrons in very high Landau levels, especially the microwave-induced resistance oscillation (MIRO) and the zero-resistance state (ZRS), have been the focus of intensive experimental^{1,2,3,4,5,6,7,8,9,10,11,12,13,14} and theoretical^{15,16,17,18,19,20,21,22,23,24,25,26,27,28,29,30} studies in the past few years.

Under the irradiation of a moderate microwave of frequency ω , the most striking resistance oscillations show up in the linear photoresistivity as a function of the inverse magnetic field $1/B$, featuring the periodical appearance of peak-valley pairs around $\omega/\omega_c = 1, 2, 3, \dots$ ($\omega_c = eB/m$ is the cyclotron frequency and m the electron effective mass). Fields of the cyclotron resonance and its harmonics are node points of these peak-valley pairs, having vanishing photoresistivity. In addition to these basic structures secondary peak-valley pairs were also observed in the linear resistance near certain fractional values, $\omega/\omega_c = 1/2, 1/3, 2/3$, and $3/2$. These fractional microwave-induced resistance oscillations were referred to real multiphoton participating processes.³¹ They were also referred to higher harmonic effect,⁵ the resonant series of consecutive single-photon transition,^{32,33} or microwave-induced sidebands.³⁴ Despite different scenarios have been proposed for these fractional MIROs of linear photoresistivity, they have so far been demonstrated to clearly appear only in the multiphoton-assisted scattering theory.³¹

Another notable effect recently discovered is the significant role of a dc current. A relatively weak current alone, without microwave radiation, can also induce substantial magnetoresistance oscillations and zero-differential resistance states.^{35,36,37,38,39,40,41,42,43} Simultaneous application of a finite dc current and a microwave radiation leads to very interesting and complicated oscillatory behavior of resistance and differential resistance.^{44,45,46,47,48} These facts clearly indicate that microwave-irradiated nonlinear magnetotransport is remarkably different from the

linear one. So far experimental and theoretical investigations on nonlinear MIROs have been carried out in the field range lower than cyclotron resonance and never anticipated any anomaly elsewhere. Very recent experiments by Hatke *et al.*⁴⁹ disclosed sharply distinct nonlinear transport behavior in the subharmonic fields of cyclotron resonance, seriously challenging the existing models. A nonlinear theory capable of identifying the specific mechanism responsible for fractional MIROs is highly desirable.

Our examination is based on a current-controlled scheme of photon-assisted transport,¹⁹ which deals with a 2D system of short thermalization time having N_s electrons in a unit area of the x - y plane. These electrons, subjected to a uniform magnetic field $\mathbf{B} = (0, 0, B)$ in the z direction and scattered by random impurities and by phonons in the lattice, perform an integrative drift motion when an incident microwave electric field $\mathbf{E}_{is} \sin \omega t$ irradiates on and a current flows in the plane. In terms of the center-of-mass (CM) momentum and coordinate defined as $\mathbf{P} \equiv \sum_j \mathbf{p}_{j\parallel}$ and $\mathbf{R} \equiv N_s^{-1} \sum_j \mathbf{r}_j$ with $\mathbf{p}_{j\parallel} \equiv (p_{jx}, p_{jy})$ and $\mathbf{r}_j \equiv (x_j, y_j)$ being the momentum and coordinate of the j th electron in the 2D plane, and the relative electron momentum and coordinate $\mathbf{p}'_{j\parallel} \equiv \mathbf{p}_{j\parallel} - \mathbf{P}/N_s$ and $\mathbf{r}'_j \equiv \mathbf{r}_j - \mathbf{R}$, the Hamiltonian of this system can be written as the sum of a CM part H_{cm} and a relative electron part H_{er} ,⁵⁰

$$H_{cm} = \frac{1}{2N_s m} (\mathbf{P} - N_s e \mathbf{A}(\mathbf{R}))^2 - N_s e (\mathbf{E}_0 + \mathbf{E}_t) \cdot \mathbf{R}, \quad (1)$$

$$H_{er} = \sum_j \left[\frac{1}{2m} (\mathbf{p}'_{j\parallel} - e \mathbf{A}(\mathbf{r}'_j))^2 + \frac{p_{jz}^2}{2m_z} + V(z_j) \right] + \sum_{i < j} V_c(\mathbf{r}'_i - \mathbf{r}'_j, z_i, z_j), \quad (2)$$

together with electron-impurity and electron-phonon couplings H_{ei} and H_{ep} . Here $\mathbf{A}(\mathbf{r}) = (-By, 0)$ is the vector potential of the magnetic field, \mathbf{E}_0 and \mathbf{E}_t are the

dc and ac components of the uniform electric field inside, m and m_z are, respectively, the electron effective mass parallel and perpendicular to the plane, $V(z)$ and $V_c(\mathbf{r}'_i - \mathbf{r}'_j, z_i, z_j)$ stand for the confined and Coulomb potentials.

The separation of the electron Hamiltonian into a CM part and a relative electron part amounts to look at electrons in the reference frame moving with their center of mass. The most important feature of this separation is that a spatially uniform electric field shows up only in H_{cm} , and that H_{er} is the Hamiltonian of a many particle system subject to a magnetic field *without the electric field*. This enables to deal with the relative electrons in the magnetic field *without tilting the Landau levels*.

We proceed with the Heisenberg operator equations for the rate of change of the CM velocity $\mathbf{V} = -i[\mathbf{R}, H]$: $\dot{\mathbf{V}} = -i[\mathbf{V}, H]$, and that of the relative electron energy H_{er} : $\dot{H}_{\text{er}} = -i[H_{\text{er}}, H]$. The CM coordinate \mathbf{R} and velocity \mathbf{V} in these equations can be treated classically, i.e. as the time-dependent expectation values of the CM coordinate and velocity, $\mathbf{R}(t)$ and $\mathbf{V}(t)$, such that $\mathbf{R}(t) - \mathbf{R}(t') = \int_{t'}^t \mathbf{V}(s) ds$. In the case of the steady transport under a modest radiation of single frequency it suffices to assume that the CM velocity, i.e. the electron drift velocity, consists of a dc part \mathbf{v} and a stationary time-dependent part of the form

$$\mathbf{V}(t) = \mathbf{v} + \mathbf{v}_1 \cos(\omega t) + \mathbf{v}_2 \sin(\omega t). \quad (3)$$

For high mobility and high carrier density 2D systems at low temperatures where electron-impurity and electron-phonon couplings are weak in comparison with the internal thermalization of electrons, it is good enough to carry out the statistical average of the above operator equations to leading orders in H_{ei} and H_{ep} . For this purpose we only need to know the distribution of relative electrons without being perturbed by H_{ei} or H_{ep} . The distribution function of the system described by Hamiltonian (2) without electric field, is an isotropic Fermi-type with a single temperature T_e . Such a statistical average of the above operator equations yields the following force and energy balance equations in the steady state:

$$N_s e \mathbf{E}_0 + N_s e (\mathbf{v} \times \mathbf{B}) + \mathbf{F} = 0, \quad (4)$$

$$N_s e \mathbf{E}_0 \cdot \mathbf{v} + S_p - W = 0. \quad (5)$$

Here

$$\mathbf{F} = \sum_{\mathbf{q}_{\parallel}} |U(\mathbf{q}_{\parallel})|^2 \sum_{n=-\infty}^{\infty} \mathbf{q}_{\parallel} J_n^2(\xi) \Pi_2(\mathbf{q}_{\parallel}, \omega_0 - n\omega) \quad (6)$$

is the time-averaged damping force against CM motion, S_p is the time-averaged rate of the electron energy-gain from the ac field, having an expression obtained from Eq. (6) by replacing \mathbf{q}_{\parallel} factor by $n\omega$, and W is the time-averaged rate of the electron energy-loss due to coupling with phonons. In Eq. (6), $U(\mathbf{q}_{\parallel})$ is the effective impurity potential, $J_n(\xi)$ is the Bessel function of order n ,

$\Pi_2(\mathbf{q}_{\parallel}, \Omega)$ is the imaginary part of the electron density correlation function at electron temperature T_e in the presence of the magnetic field, and $\omega_0 \equiv \mathbf{q}_{\parallel} \cdot \mathbf{v}$. The argument in $J_n(\xi)$ is $\xi \equiv \sqrt{(\mathbf{q}_{\parallel} \cdot \mathbf{v}_1)^2 + (\mathbf{q}_{\parallel} \cdot \mathbf{v}_2)^2} / \omega$.

The ac components \mathbf{v}_1 and \mathbf{v}_2 of the electron drift velocity should be determined selfconsistently from the incident ac field \mathbf{E}_{is} by the Maxwell equations connecting both sides of the 2DEG, taking account the scattering-related damping forces \mathbf{F}_s and \mathbf{F}_c .¹⁹ However, for the high-mobility systems at low temperatures, the effects of these scattering-related forces are much weaker than that of radiative decay³⁰ and always negligible, whence \mathbf{v}_1 and \mathbf{v}_2 are directly determined by the setup of the 2DEG in the sample substrate.¹⁹

The effect of interparticle Coulomb interaction is included in the density correlation function to the degree of electron level broadening and screening (considered in the effective impurity and phonon potentials). The remaining $\Pi_2(\mathbf{q}_{\parallel}, \Omega)$ function in Eqs. (6) is that of a non-interacting 2D electron gas in the magnetic field, which can be written in the Landau representation as⁵¹

$$\begin{aligned} \Pi_2(\mathbf{q}_{\parallel}, \Omega) &= \frac{1}{2\pi l_B^2} \sum_{n, n'} C_{n, n'} (l_B^2 q_{\parallel}^2 / 2) \Pi_2(n, n', \Omega), \quad (7) \\ \Pi_2(n, n', \Omega) &= -\frac{2}{\pi} \int d\varepsilon [f(\varepsilon) - f(\varepsilon + \Omega)] \\ &\quad \times \text{Im}G_n(\varepsilon + \Omega) \text{Im}G_{n'}(\varepsilon), \quad (8) \end{aligned}$$

where $l_B = \sqrt{1/|eB|}$ is the magnetic length, $C_{n, n+l}(Y) \equiv n![(n+l)!]^{-1} Y^l e^{-Y} [L_n^l(Y)]^2$ with $L_n^l(Y)$ the associate Laguerre polynomial, $f(\varepsilon) = \{\exp[(\varepsilon - \mu)/T_e] + 1\}^{-1}$ is the Fermi function at electron temperature T_e , and $\text{Im}G_n(\varepsilon)$ is the density-of-states of the broadened Landau level n .

We model the density-of-states function with a Gaussian form for both overlapped and separated Landau levels ($\varepsilon_n = n\omega_c$ is the center of the n th Landau level):

$$\text{Im}G_n(\varepsilon) = -(2\pi)^{\frac{1}{2}} \Gamma^{-1} \exp[-2(\varepsilon - \varepsilon_n)^2 / \Gamma^2] \quad (9)$$

with a $B^{1/2}$ dependent half width $\Gamma = (8\alpha e\omega_c / \pi m\mu_0)^{1/2}$ expressed in terms of μ_0 , the linear mobility in the absence of the magnetic field, together with a broadening parameter α to take account the difference of the transport scattering time from the broadening-related quantum lifetime.^{3,18}

These formulations are convenient for current-driven nonlinear magnetotransport of any configuration. For an isotropic system where the frictional force \mathbf{F} is in the opposite direction of the drift velocity \mathbf{v} and the magnitudes of both the frictional force and the energy-loss rate depend only on $v \equiv |\mathbf{v}|$, we can write $\mathbf{F}(\mathbf{v}) = F(v)\mathbf{v}/v$ and $W(\mathbf{v}) = W(v)$. In the Hall configuration with velocity \mathbf{v} in the x direction $\mathbf{v} = (v, 0, 0)$ or the current density $J_x = J = N_s e v$ and $J_y = 0$, Eq. (4) yields the longitudinal differential resistivity r_{xx} at given v as

$$r_{xx} = -(\partial F(v)/\partial v)/(N_s^2 e^2). \quad (10)$$

In the linear case, the resistivity r_{xx} oscillations (peak-valley pairs) result from the resonant real photon-assisted electron transitions between different Landau levels.³¹ We denote a real-photon assisted process in which an electron jumps across l Landau-level (LL) spacings with the assistance (emission or absorption) of n photons as $n\omega:l\omega_c$, or $n:l$. This process contributes, in the r_{xx} - ω/ω_c curve, a pair structure consisting of a maximum and a minimum on both sides of $\omega/\omega_c = l/n$.

Thus, the single-photon process 1:1, the two-photon process 2:2, the three-photon process 3:3, ..., all contribute to the maximum–minimum pair around $\omega/\omega_c = 1$; the two-photon process 2:1, the 4-photon process 4:2, ..., all contribute to the maximum–minimum pair around $\omega/\omega_c = 1/2$; the 3-photon process 3:1, the 6-photon process 6:2, ..., all contribute to the maximum–minimum pair around $\omega/\omega_c = 1/3$; etc. The virtual photon process (zero-photon process) during which the electron may absorb (emit) one or several photons and then emits (absorbs) them before finishing an intra-LL transition (assuming separated LLs for convenience), which can be denoted as 0:0, gives rise to an overall resistivity suppression without structure.³¹

The effects of a finite current show up as the energy (frequency) shift $\omega_0 = \mathbf{q}_{\parallel} \cdot \mathbf{v}$ in the density-correlation function $\Pi_2(\mathbf{q}_{\parallel}, \Omega)$ in Eq. (6). This energy shift indicates that an electron having momentum \mathbf{q}_{\parallel} participating in the system integrative drift motion of velocity \mathbf{v} carries an extra energy $\mathbf{q}_{\parallel} \cdot \mathbf{v}$ during its transition. In the case of low temperature (T_e much less than the Fermi energy ε_F) and large Landau-level filling factor ($\nu = \varepsilon_F/\omega_c \gg 1$), the major contributions to the summation in Eq. (7) come from terms $n \sim n' \sim \nu$, then the function $C_{n,n'}(x)$ has a sharp principal maximum near $x = 4\nu$. Therefore, as a function of the in-plane momentum q_{\parallel} , $\Pi_2(\mathbf{q}_{\parallel}, \Omega)$ sharply peaks around $q_{\parallel} \simeq 2k_F$. As the composite effect of this energy shift, an electron possesses an extra energy $\omega_j \equiv 2k_F v = \sqrt{8\pi/N_s} J/e$ for its transition in addition to those provided by photons.

Therefore, the resonant condition applied in the linear case for electron scattering across l LL-spacings with the assistance (emission or absorption) of n photons, $n\omega = l\omega_c$, should change to

$$\omega_j \pm n\omega = \pm l\omega_c \quad (n = 0, 1, 2, \dots, l = 0, 1, 2, \dots) \quad (11)$$

when the system has an integrative motion of velocity v , i.e. a finite current density $J = N_s e v$. We can still use symbol $n:l$ to denote this process. We will also use symbol $n-$ to represent all the n -photon participating processes (electron may jump across any LL spacings).

The increase of the current density from zero reduces the rates of the scattering processes resonant in the linear case, such as those of zero-photon processes 0:0 everywhere, of single-photon process 1:1 and 2-photon process 2:2 at $\omega/\omega_c = 1$, of 2-photon processes 2:1 and 4-photon processes 4:2 at $\omega/\omega_c = 1/2$. But it may increase the rates of the scattering processes originally absent or very small in the linear case, such as those of single-photon

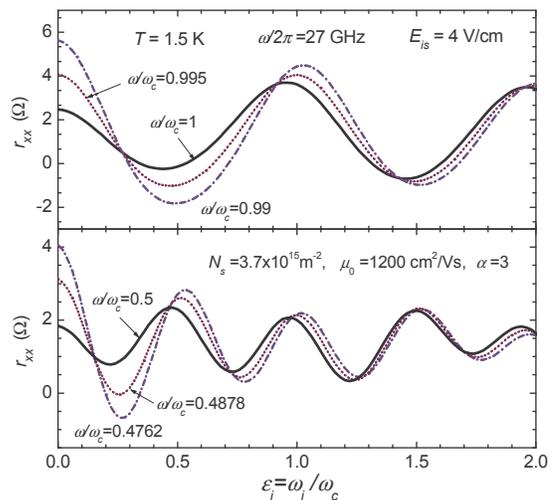


FIG. 1: (Color online) Magnetoresistivity r_{xx} vs $\epsilon_j = \omega_j/\omega_c$ at $\omega/\omega_c = 1, 0.995, 0.99, 0.5, 0.4878$ and 0.4762 .

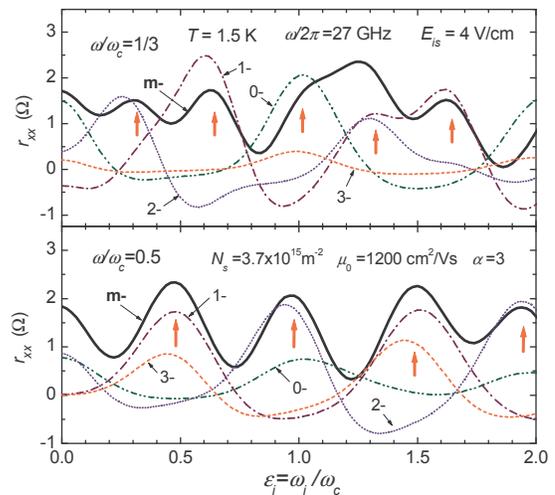


FIG. 2: (Color online) Magnetoresistivity r_{xx} vs ϵ_j at $\omega/\omega_c = 1/3$ and 0.5 . Curves with 0-, 1-, 2-, 3- and m- are separated contributions from 0-, 1-, 2-, 3- and multi-photon processes.

process 1:1 and 3-photon process 3:1 at $\omega/\omega_c = 1/2$.

At cyclotron resonance and its harmonics $\omega/\omega_c = 1, 2, 4, \dots$, the resonant condition (11) can be satisfied only at $\epsilon_j \equiv \omega_j/\omega_c = 0, 1, 2, \dots$, where the scattering rate peaks and the differential resistivity exhibits maximum. Therefore, at these magnetic fields the r_{xx} oscillation with changing ϵ_j always has a periodicity $\Delta\epsilon_j \approx 1$.

The situation changes near subharmonic cyclotron resonant fields. For instance, at $\omega/\omega_c = 1/2$, the resonant condition (11) for 0-, 2- and 4-photon processes ($n = 0, 2$ and 4) is satisfied at $\epsilon_j = 0, 1, 2, \dots$, indicating these even-photon processes contribute resistivity maxima there. At $\epsilon_j = 0.5, 1.5, \dots$, on the other hand, the resonant condition (11) is satisfied for 1- and 3-photon processes ($n = 1$ and 3), indicating these odd-photon processes contribute resistivity maxima. Because of this, the period of r_{xx} oscillation with ϵ_j may shrink to $\Delta\epsilon_j \approx 0.5$, or the oscil-

lation frequency doubles, at $\omega/\omega_c = 1/2$.

At the 3rd subharmonic field, $\omega/\omega_c = 1/3$, in addition to the appearance of resonant scattering of 0- and 3-photon processes at $\epsilon_j = 0, 1$ and 2 , the resonance scattering can also appear at $\epsilon_j = 1/3, 4/3$ and $5/3$ for 2-photon processes and at $\epsilon_j = 2/3, 4/3$ and $5/3$ for single-photon processes, leading to possible shrinkage of the r_{xx} oscillation period to $\epsilon_j \approx 1/3$, or the frequency tripling.

These analyses are confirmed by the numerical results shown in Figs. 1 and 2, where we plot the differential resistivity r_{xx} calculated from Eq. (10) as a function of the normalized current density $\epsilon_j = \omega_j/\omega_c$ for a GaAs-based system of $N_s = 3.7 \times 10^{15} \text{ m}^{-2}$ and $\mu_0 = 1200 \text{ m}^2/\text{Vs}$ at $T = 1.5 \text{ K}$, irradiated by a 27 GHz microwave having incident electric field amplitude $E_{is} = 4.0 \text{ V/cm}$. The elastic scatterings are due to a mixture of short-range and background impurities, and the broadening parameter $\alpha = 3$, or the LL width $2\Gamma/\omega_c \simeq 0.63(\omega/\omega_c)^{1/2}$, in

the separated LL regime for $\omega/\omega_c < 1$. The predicted r_{xx} behavior near $\omega/\omega_c = 0.5$ are in excellent agreement with recent experimental findings.⁴⁹

In summary, the electron in a dc-driven system having an integrative drift velocity v carries an extra average energy $\omega_j = 2k_F v$ in its transition between LLs, giving rise to a current-dependent resonance condition. The peaks of the differential resistivity r_{xx} arise from resonant multiphoton assisted scatterings of electron jumping across l LL spacings. The current-induced consecutive emergence of different resonant multi-photon processes results in the frequency doubling and tripling of the resistance oscillations near the 2nd and 3rd subharmonic fields.

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